Preface

Materials Research Society Symposium Proceedings

Copper CMP

Challenges and Rewards of Low-Abrasive Copper CMP: Evaluation and Integration for Single-Damascene Cu/Low-k Interconnects for the 90 nm Node

Investigation of the Influence of Different Copper Slurry Systems on Post CMP Topography Performance

Copper CMP Formulation for 65 nm Device Planarization

Effect of Hydrogen Peroxide on Oxidation of Copper in CMP Slurries Containing Glycine and Cu Sulfate

Modified Abrasives Based on Fumed SiO\textsubscript{2} and Al\textsubscript{2}O\textsubscript{3} for the Cu CMP Process

Novel Pure Organic Particles for Copper CMP at Low Down Force

Effect of Nano-Size Silica Abrasives in Chemical Mechanical Polishing of Copper

Metal CMP Modeling

A Model of Cu-CMP

Coherent Chip-Scale Modeling for Copper CMP Pattern Dependence

Planarization Equipment

Polish Profile Control Using Magnetic Control Head

Adaptive Piezo-Controlled Carrier for CMP Processing

Metrological Assessment of the Coefficient of Friction of Various Types of Silica Using the Motor Current During ILD-CMP

Poster Session

A Study on the Self-Stopping CMP Process for the Planarization of the High Step Height(@step height\textgreater than sign)1.5 um) Pattern

Modeling of Pattern Density Dependent Pressure Non-Uniformity at a Die Scale for ILD Chemical Mechanical Planarization

Effect of Abrasive in Cu-CMP Slurry on Global Planarization

Investigation of Mechanical Integrity and Its Effect on Polishing for Novel Polyurethane Polishing Pad

Interaction Between Abrasive Particles and Film Surfaces in Low Down Force Cu CMP

Effect of Particle Interaction on Agglomeration of Silica-Based CMP Slurries

Measurement of Electroplated Copper Overburden for Advanced Process Development and Control

Polishing Pads

Micro Feature Pad Development and Its Performance in Chemical Mechanical Planarization

Characterization of CMP Pad Surface Texture and Pad-Wafer Contact

Modeling CMP Transport and Kinetics at the Pad Groove Scale

In Situ Friction and Pad Topography Measurements During CMP

Metrology of Psiloquest's Application Specific Pads (ASP) for CMP Applications

CMP Corrosion and Cleaning

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